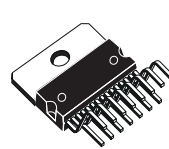


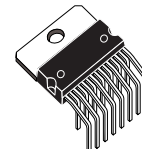
100V - 100W DMOS AUDIO AMPLIFIER WITH MUTE/ST-BY

- VERY HIGH OPERATING VOLTAGE RANGE ($\pm 40V$)
- DMOS POWER STAGE
- HIGH OUTPUT POWER (UP TO 100W MUSIC POWER)
- MUTING/STAND-BY FUNCTIONS
- NO SWITCH ON/OFF NOISE
- NO BOUCHEROT CELLS
- VERY LOW DISTORTION
- VERY LOW NOISE
- SHORT CIRCUIT PROTECTION
- THERMAL SHUTDOWN

MULTIPOWER BCD TECHNOLOGY



Multiwatt15V



Multiwatt15H

ORDERING NUMBERS:

TDA7294V

TDA7294HS

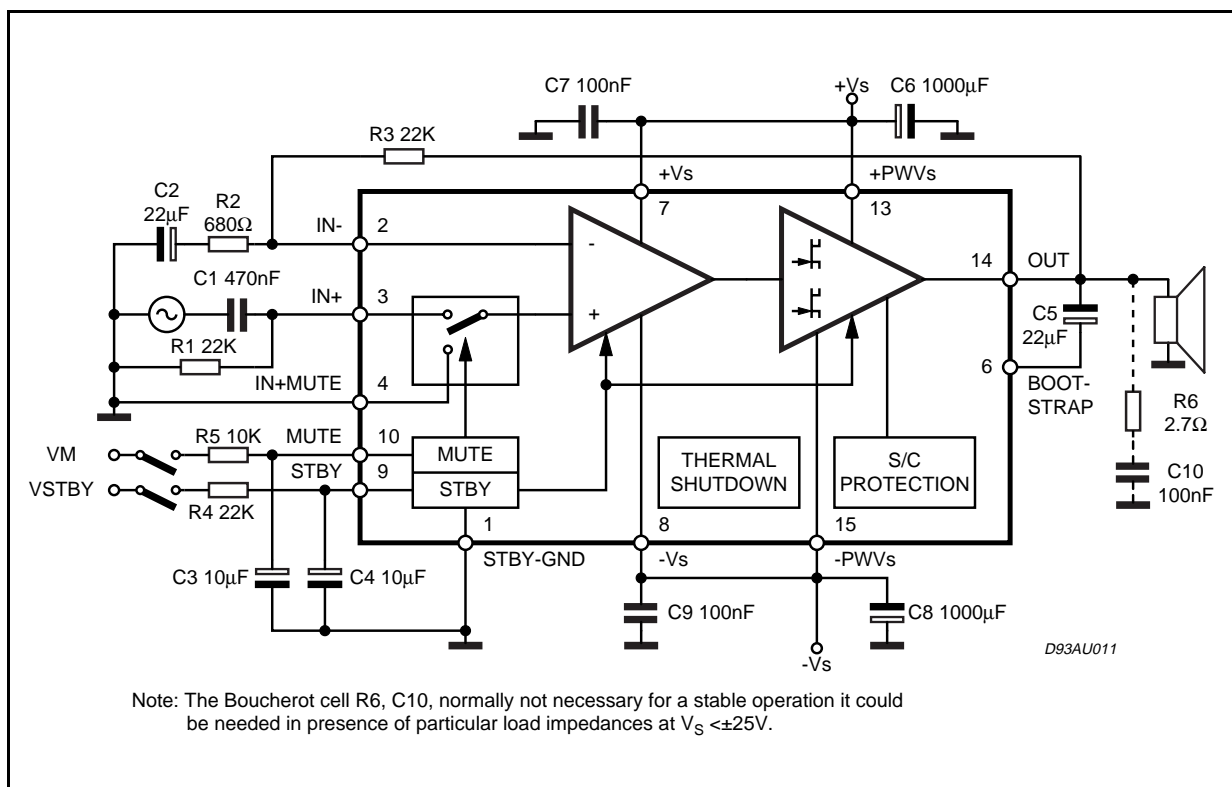
DESCRIPTION

The TDA7294 is a monolithic integrated circuit in Multiwatt15 package, intended for use as audio class AB amplifier in Hi-Fi field applications (Home Stereo, self powered loudspeakers, Top-class TV). Thanks to the wide voltage range and

to the high out current capability it is able to supply the highest power into both 4 Ω and 8 Ω loads even in presence of poor supply regulation, with high Supply Voltage Rejection.

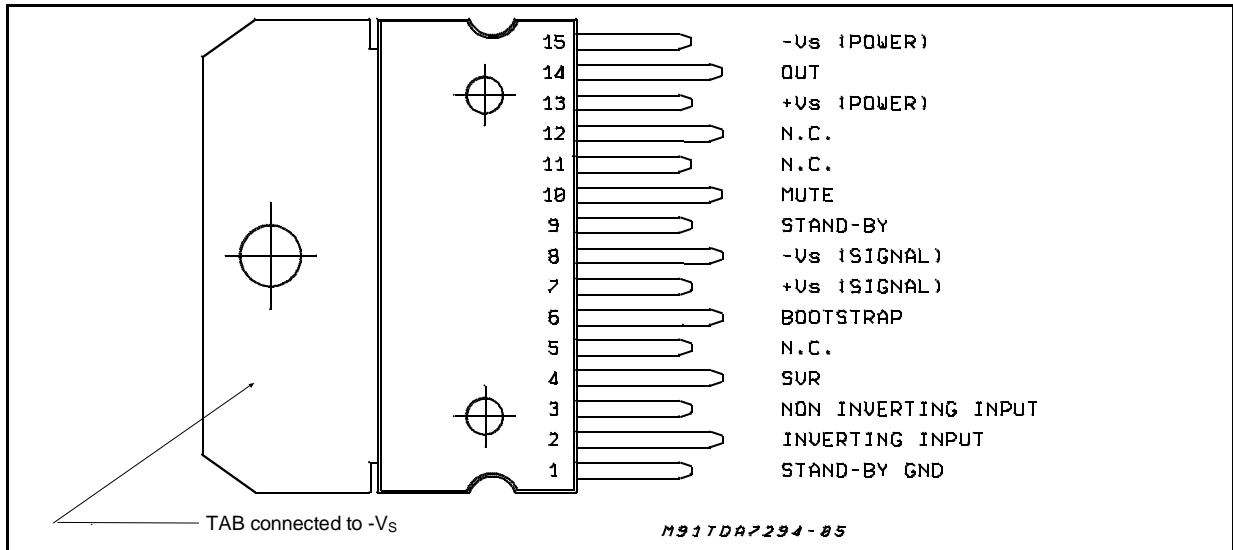
The built in muting function with turn on delay simplifies the remote operation avoiding switching on-off noises.

Figure 1: Typical Application and Test Circuit

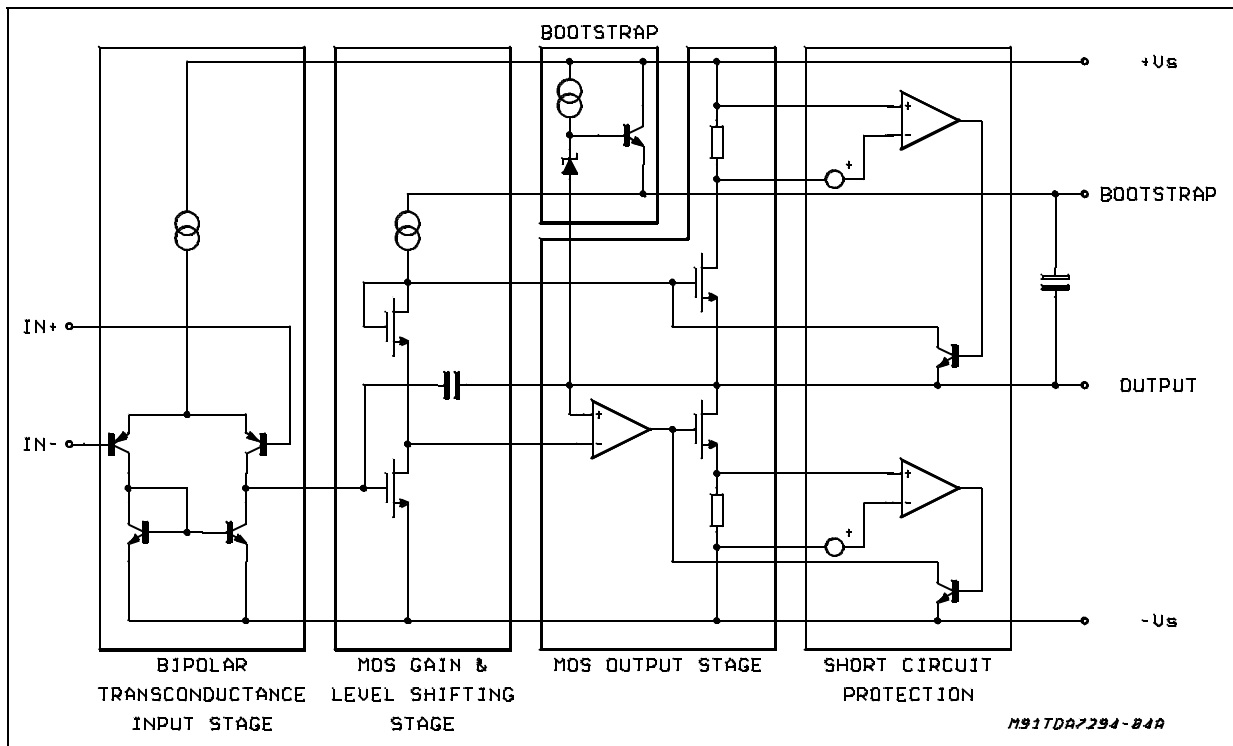


TDA7294

PIN CONNECTION (Top view)



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|----------------|---|----------|------------|
| V_s | Supply Voltage (No Signal) | ± 50 | V |
| I_o | Output Peak Current | 10 | A |
| P_{tot} | Power Dissipation $T_{case} = 70^\circ C$ | 50 | W |
| T_{op} | Operating Ambient Temperature Range | 0 to 70 | $^\circ C$ |
| T_{stg}, T_j | Storage and Junction Temperature | 150 | $^\circ C$ |

THERMAL DATA

| Symbol | Description | Value | Unit |
|------------------|----------------------------------|-------|----------|
| $R_{th\ j-case}$ | Thermal Resistance Junction-case | Max | 1.5 °C/W |

ELECTRICAL CHARACTERISTICS (Refer to the Test Circuit $V_S = \pm 35V$, $R_L = 8\Omega$, $G_V = 30dB$; $R_g = 50\Omega$; $T_{amb} = 25^\circ C$, $f = 1\text{ kHz}$; unless otherwise specified.

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Unit |
|--|---|--|----------------|-------------------|-----------|--------------------|
| V_S | Supply Range | | ± 10 | | ± 40 | V |
| I_q | Quiescent Current | | 20 | 30 | 65 | mA |
| I_b | Input Bias Current | | | | 500 | nA |
| V_{OS} | Input Offset Voltage | | | | ± 10 | mV |
| I_{OS} | Input Offset Current | | | | ± 100 | nA |
| P_O | RMS Continuous Output Power | d = 0.5%: $V_S = \pm 35V$, $R_L = 8\Omega$ $V_S = \pm 31V$, $R_L = 6\Omega$ $V_S = \pm 27V$, $R_L = 4\Omega$ | 60 60 60 | 70 70 70 | | W W W |
| | Music Power (RMS) IEC268.3 RULES - $\Delta t = 1s$ (*) | d = 10% $R_L = 8\Omega$; $V_S = \pm 38V$ $R_L = 6\Omega$; $V_S = \pm 33V$ $R_L = 4\Omega$; $V_S = \pm 29V$ (***) | | 100 100 100 | | W W W |
| d | Total Harmonic Distortion (**) | $P_O = 5W$; $f = 1kHz$ $P_O = 0.1$ to $50W$; $f = 20Hz$ to $20kHz$ | | 0.005 | 0.1 | % % |
| | | $V_S = \pm 27V$, $R_L = 4\Omega$: $P_O = 5W$; $f = 1kHz$ $P_O = 0.1$ to $50W$; $f = 20Hz$ to $20kHz$ | | 0.01 | 0.1 | % % |
| SR | Slew Rate | | 7 | 10 | | V/ μs |
| G_V | Open Loop Voltage Gain | | | 80 | | dB |
| G_V | Closed Loop Voltage Gain | | 24 | 30 | 40 | dB |
| e_N | Total Input Noise | A = curve $f = 20Hz$ to $20kHz$ | | 1 2 | 5 | μV μV |
| f_L, f_H | Frequency Response (-3dB) | $P_O = 1W$ | 20Hz to 20kHz | | | |
| R_i | Input Resistance | | 100 | | | k Ω |
| SVR | Supply Voltage Rejection | $f = 100Hz$; $V_{ripple} = 0.5V_{rms}$ | 60 | 75 | | dB |
| T_S | Thermal Shutdown | | | 145 | | $^\circ C$ |
| STAND-BY FUNCTION (Ref: $-V_S$ or GND) | | | | | | |
| $V_{ST\ on}$ | Stand-by on Threshold | | | | 1.5 | V |
| $V_{ST\ off}$ | Stand-by off Threshold | | 3.5 | | | V |
| ATT_{st-by} | Stand-by Attenuation | | 70 | 90 | | dB |
| $I_{q\ st-by}$ | Quiescent Current @ Stand-by | | | 1 | 3 | mA |
| MUTE FUNCTION (Ref: $-V_S$ or GND) | | | | | | |
| V_{Mon} | Mute on Threshold | | | | 1.5 | V |
| V_{Moff} | Mute off Threshold | | 3.5 | | | V |
| ATT_{mute} | Mute Attenuation | | 60 | 80 | | dB |

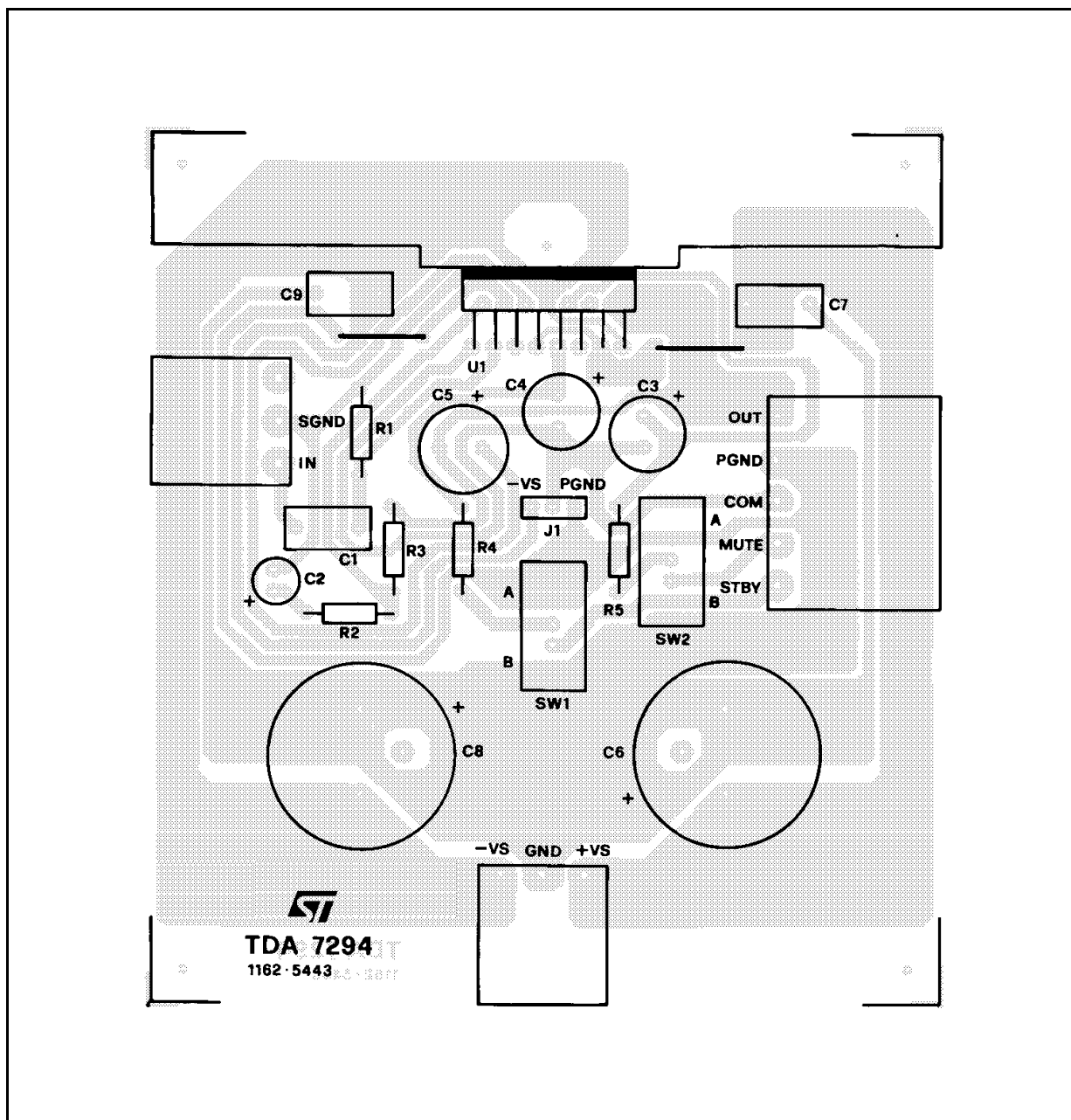
Note (*):**MUSIC POWER CONCEPT**

MUSIC POWER is the maximal power which the amplifier is capable of producing across the rated load resistance (regardless of non linearity) 1 sec after the application of a sinusoidal input signal of frequency 1KHz.

Note ():** Tested with optimized Application Board (see fig. 2)

Note (*):** Limited by the max. allowable current.

Figure 2: P.C.B. and components layout of the circuit of figure 1. (1:1 scale)



Note:

The Stand-by and Mute functions can be referred either to GND or -VS.
 On the P.C.B. is possible to set both the configuration through the jumper J1.

APPLICATION SUGGESTIONS (see Test and Application Circuits of the Fig. 1)

The recommended values of the external components are those shown on the application circuit of Figure 1. Different values can be used; the following table can help the designer.

| COMPONENTS | SUGGESTED VALUE | PURPOSE | LARGER THAN SUGGESTED | SMALLER THAN SUGGESTED |
|------------|-----------------|-----------------------------------|--------------------------|--------------------------------------|
| R1 (*) | 22k | INPUT RESISTANCE | INCREASE INPUT IMPEDANCE | DECREASE INPUT IMPEDANCE |
| R2 | 680Ω | CLOSED LOOP GAIN SET TO 30dB (**) | DECREASE OF GAIN | INCREASE OF GAIN |
| R3 (*) | 22k | | INCREASE OF GAIN | DECREASE OF GAIN |
| R4 | 22k | ST-BY TIME CONSTANT | LARGER ST-BY ON/OFF TIME | SMALLER ST-BY ON/OFF TIME; POP NOISE |
| R5 | 10k | MUTE TIME CONSTANT | LARGER MUTE ON/OFF TIME | SMALLER MUTE ON/OFF TIME |
| C1 | 0.47μF | INPUT DC DECOUPLING | | HIGHER LOW FREQUENCY CUTOFF |
| C2 | 22μF | FEEDBACK DC DECOUPLING | | HIGHER LOW FREQUENCY CUTOFF |
| C3 | 10μF | MUTE TIME CONSTANT | LARGER MUTE ON/OFF TIME | SMALLER MUTE ON/OFF TIME |
| C4 | 10μF | ST-BY TIME CONSTANT | LARGER ST-BY ON/OFF TIME | SMALLER ST-BY ON/OFF TIME; POP NOISE |
| C5 | 22μF | BOOTSTRAPPING | | SIGNAL DEGRADATION AT LOW FREQUENCY |
| C6, C8 | 1000μF | SUPPLY VOLTAGE BYPASS | | DANGER OF OSCILLATION |
| C7, C9 | 0.1μF | SUPPLY VOLTAGE BYPASS | | DANGER OF OSCILLATION |

(*) R1 = R3 FOR POP OPTIMIZATION

(**) CLOSED LOOP GAIN HAS TO BE ≥ 24 dB

TYPICAL CHARACTERISTICS

(Application Circuit of fig 1 unless otherwise specified)

Figure 3: Output Power vs. Supply Voltage.

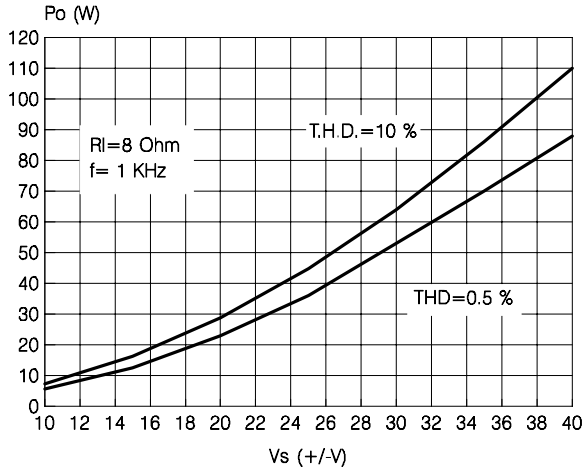


Figure 4: Distortion vs. Output Power

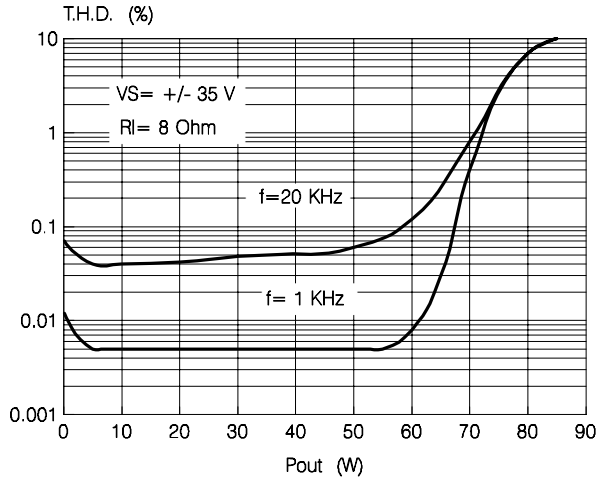


Figure 5: Output Power vs. Supply Voltage

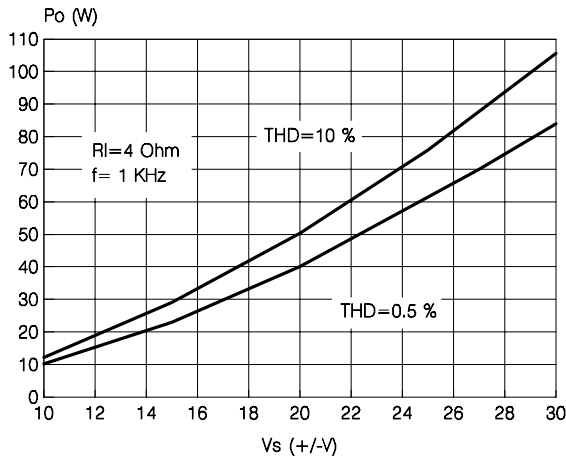


Figure 6: Distortion vs. Output Power

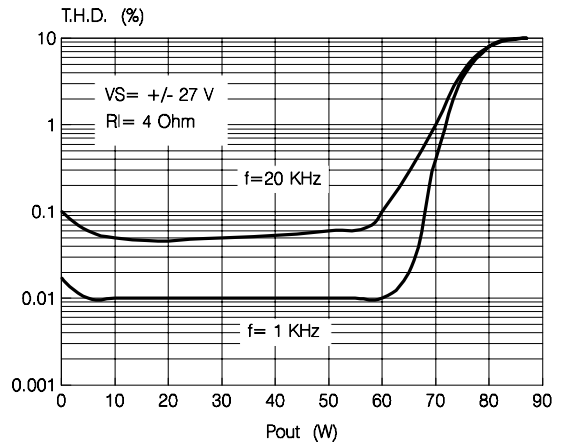


Figure 7: Distortion vs. Frequency

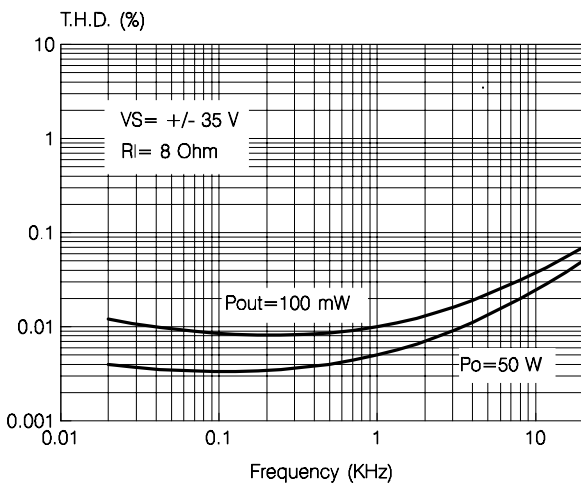
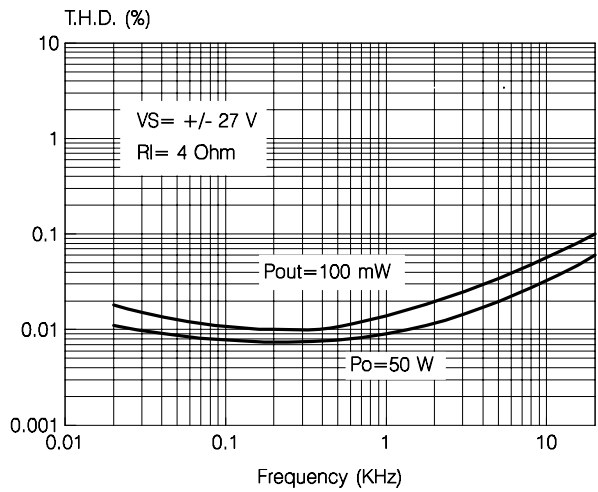


Figure 8: Distortion vs. Frequency



TYPICAL CHARACTERISTICS (continued)

Figure 9: Quiescent Current vs. Supply Voltage

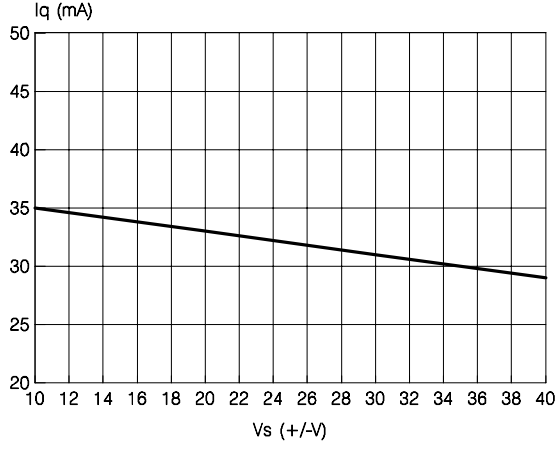


Figure 10: Supply Voltage Rejection vs. Frequency

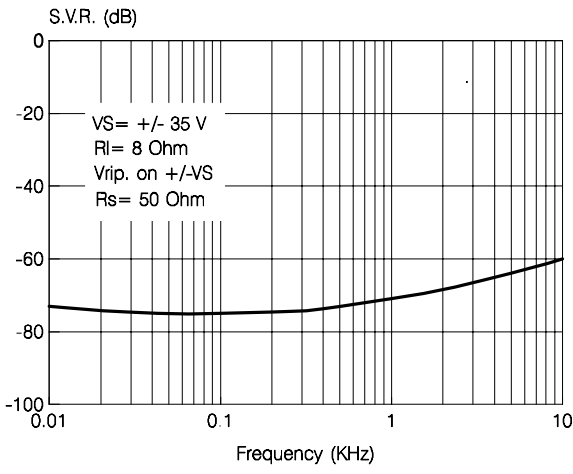


Figure 11: Mute Attenuation vs. V_{pin10}

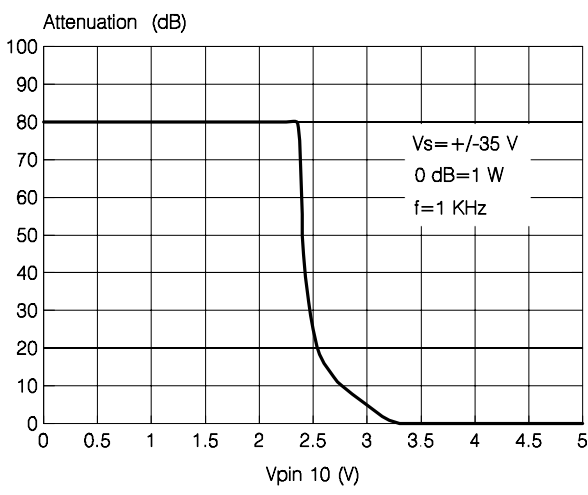


Figure 12: St-by Attenuation vs. V_{pin9}

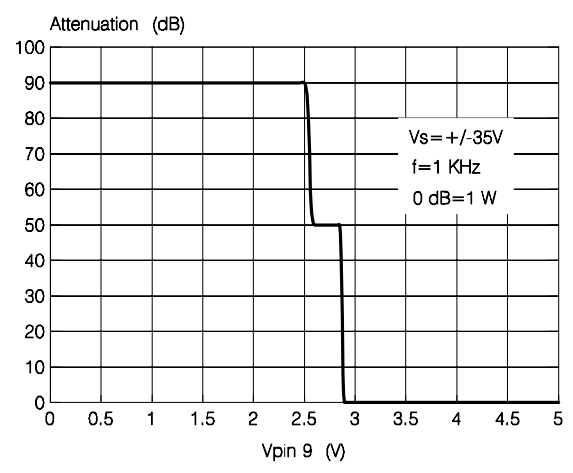


Figure 13: Power Dissipation vs. Output Power

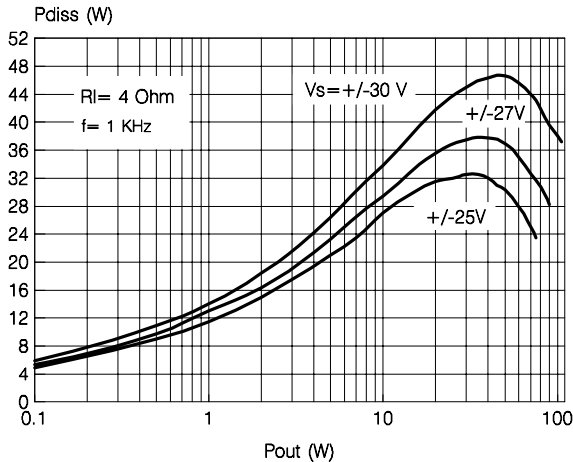
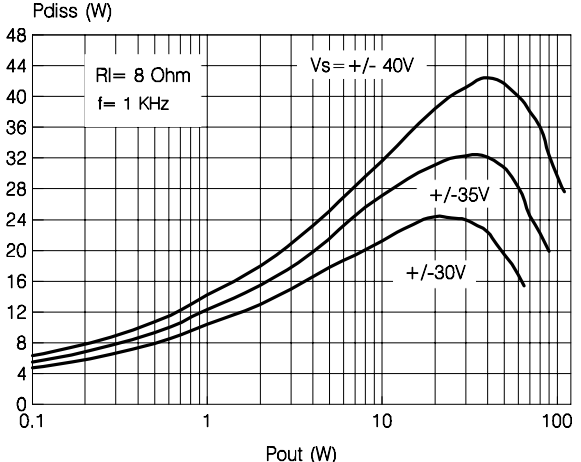


Figure 14: Power Dissipation vs. Output Power



INTRODUCTION

In consumer electronics, an increasing demand has arisen for very high power monolithic audio amplifiers able to match, with a low cost the performance obtained from the best discrete designs.

The task of realizing this linear integrated circuit in conventional bipolar technology is made extremely difficult by the occurrence of 2nd breakdown phenomenon. It limits the safe operating area (SOA) of the power devices, and as a consequence, the maximum attainable output power, especially in presence of highly reactive loads.

Moreover, full exploitation of the SOA translates into a substantial increase in circuit and layout complexity due to the need for sophisticated protection circuits.

To overcome these substantial drawbacks, the use of power MOS devices, which are immune from secondary breakdown is highly desirable.

The device described has therefore been developed in a mixed bipolar-MOS high voltage technology called BCD 100.

1) Output Stage

The main design task one is confronted with while developing an integrated circuit as a power operational amplifier, independently of the technology used, is that of realizing the output stage.

The solution shown as a principle schematic by Fig 15 represents the DMOS unity-gain output buffer of the TDA7294.

This large-signal, high-power buffer must be capable of handling extremely high current and voltage levels while maintaining acceptably low harmonic distortion and good behaviour over frequency response; moreover, an accurate control of quiescent current is required.

A local linearizing feedback, provided by differential amplifier A, is used to fulfill the above requirements, allowing a simple and effective quiescent current setting.

Proper biasing of the power output transistors alone is however not enough to guarantee the absence of crossover distortion.

While a linearization of the DC transfer characteristic of the stage is obtained, the dynamic behaviour of the system must be taken into account.

A significant aid in keeping the distortion contributed by the final stage as low as possible is provided by the compensation scheme, which exploits the direct connection of the Miller capacitor at the amplifier's output to introduce a local AC feedback path enclosing the output stage itself.

2) Protections

In designing a power IC, particular attention must be reserved to the circuits devoted to protection of the device from short circuit or overload conditions.

Due to the absence of the 2nd breakdown phenomenon, the SOA of the power DMOS transistors is delimited only by a maximum dissipation curve dependent on the duration of the applied stimulus.

In order to fully exploit the capabilities of the power transistors, the protection scheme implemented in this device combines a conventional SOA protection circuit with a novel local temperature sensing technique which "dynamically" controls the maximum dissipation.

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In order to fully exploit the capabilities of the power transistors, the protection scheme implemented in this device combines a conventional SOA protection circuit with a novel local temperature sensing technique which "dynamically" controls the maximum dissipation.

Figure 15: Principle Schematic of a DMOS unity-gain buffer.

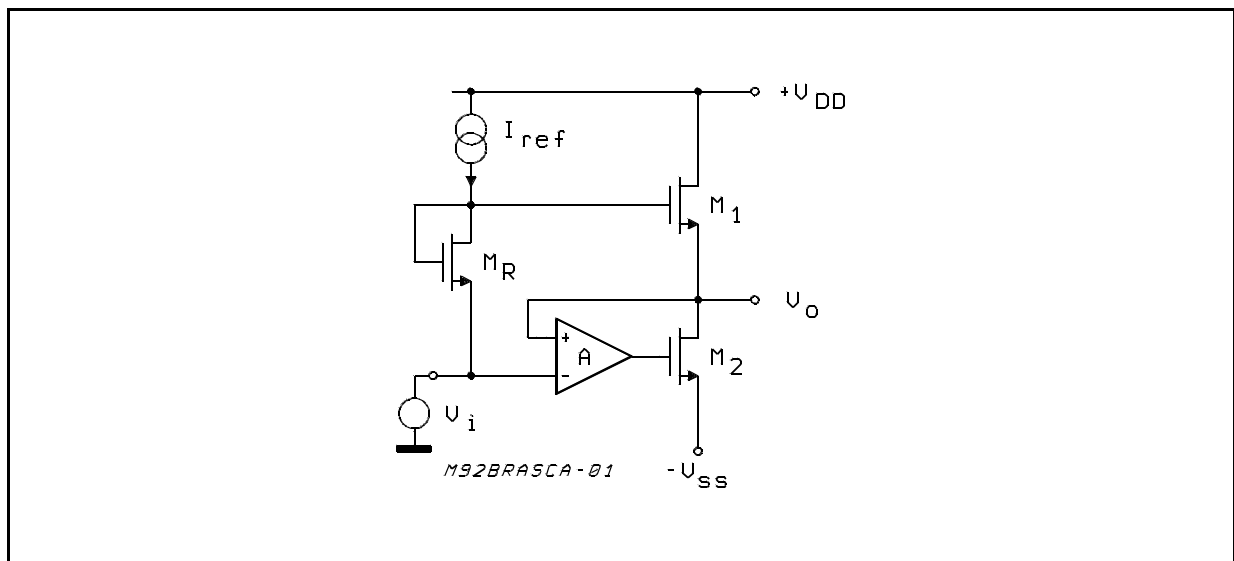
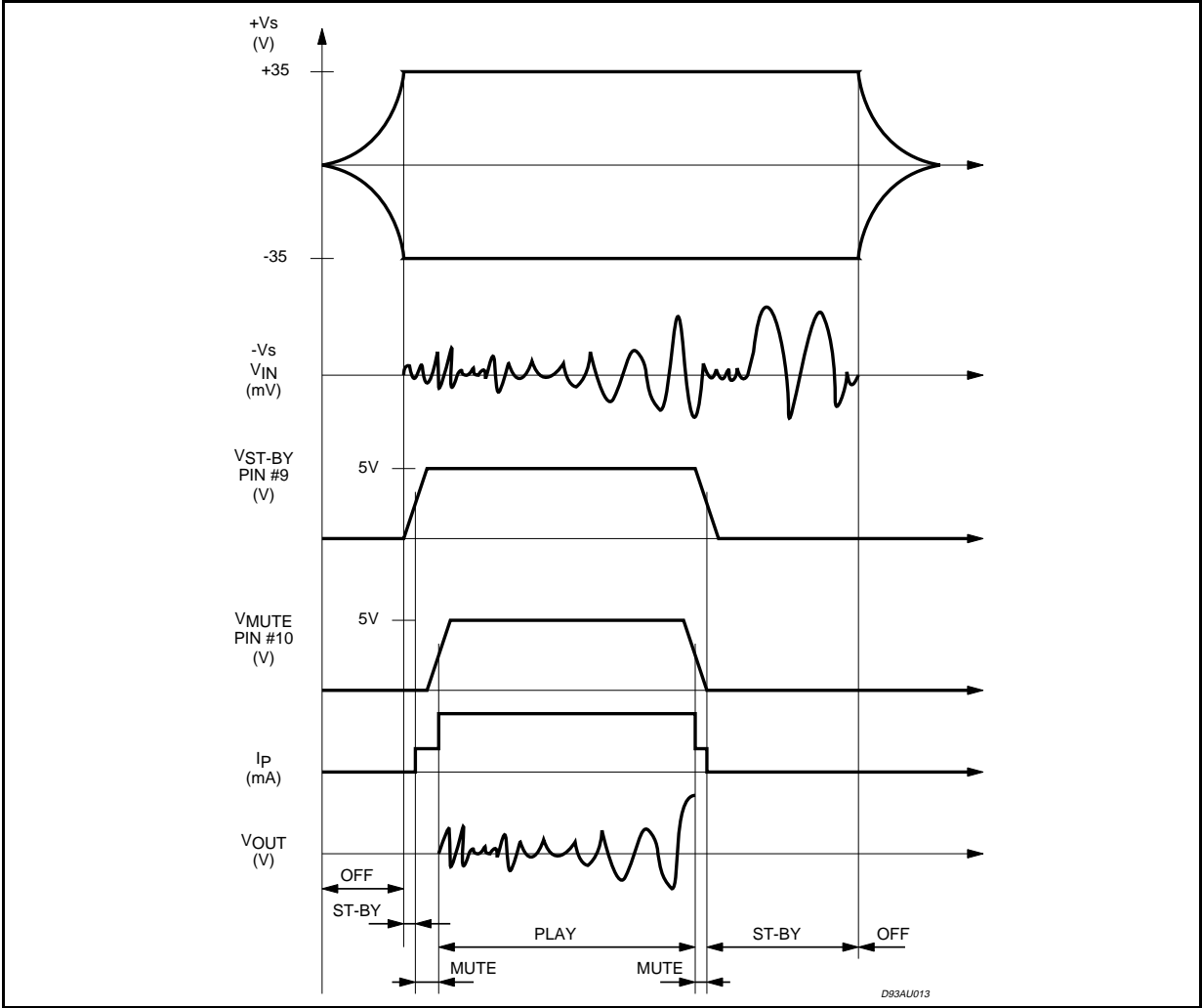


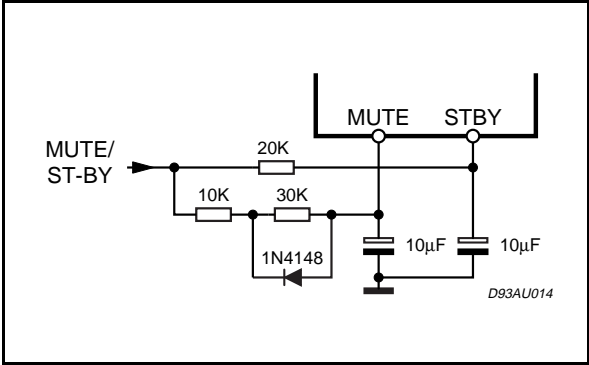
Figure 16: Turn ON/OFF Suggested Sequence



In addition to the overload protection described above, the device features a thermal shutdown circuit which initially puts the device into a muting state (@ $T_j = 145^\circ\text{C}$) and then into stand-by (@

$T_j = 150^\circ\text{C}$). Full protection against electrostatic discharges on every pin is included.

Figure 17: Single Signal ST-BY/MUTE Control Circuit



3) Other Features

The device is provided with both stand-by and mute functions, independently driven by two CMOS logic compatible input pins.

The circuits dedicated to the switching on and off of the amplifier have been carefully optimized to avoid any kind of uncontrolled audible transient at the output.

The sequence that we recommend during the ON/OFF transients is shown by Figure 16.

The application of figure 17 shows the possibility of using only one command for both st-by and mute functions. On both the pins, the maximum applicable range corresponds to the operating supply voltage.

APPLICATION INFORMATION
HIGH-EFFICIENCY

Constraints of implementing high power solutions are the power dissipation and the size of the power supply. These are both due to the low efficiency of conventional AB class amplifier approaches.

Here below (figure 18) is described a circuit proposal for a high efficiency amplifier which can be adopted for both HI-FI and CAR-RADIO applications.

The TDA7294 is a monolithic MOS power amplifier which can be operated at 80V supply voltage (100V with no signal applied) while delivering output currents up to ±10 A.

This allows the use of this device as a very high power amplifier (up to 180W as peak power with T.H.D.=10 % and $R_L = 4 \text{ Ohm}$); the only drawback is the power dissipation, hardly manageable in the above power range.

Figure 20 shows the power dissipation versus output power curve for a class AB amplifier, compared with a high efficiency one.

In order to dimension the heatsink (and the power supply), a generally used average output power value is one tenth of the maximum output power at T.H.D.=10 %.

From fig. 20, where the maximum power is around 200 W, we get an average of 20 W, in this condition, for a class AB amplifier the average power dissipation is equal to 65 W.

The typical junction-to-case thermal resistance of the TDA7294 is $1 \text{ }^\circ\text{C/W}$ (max= $1.5 \text{ }^\circ\text{C/W}$). To avoid that, in worst case conditions, the chip temperature exceeds $150 \text{ }^\circ\text{C}$, the thermal resistance of the heatsink must be $0.038 \text{ }^\circ\text{C/W}$ (@ max ambient temperature of $50 \text{ }^\circ\text{C}$).

As the above value is practically unreachable; a high efficiency system is needed in those cases where the continuous RMS output power is higher than 50-60 W.

The TDA7294 was designed to work also in higher efficiency way.

For this reason there are four power supply pins: two intended for the signal part and two for the power part.

T1 and T2 are two power transistors that only operate when the output power reaches a certain threshold (e.g. 20 W). If the output power increases, these transistors are switched on during the portion of the signal where more output voltage swing is needed, thus "bootstrapping" the power supply pins (#13 and #15).

The current generators formed by T4, T7, zener

Figure 18: High Efficiency Application Circuit

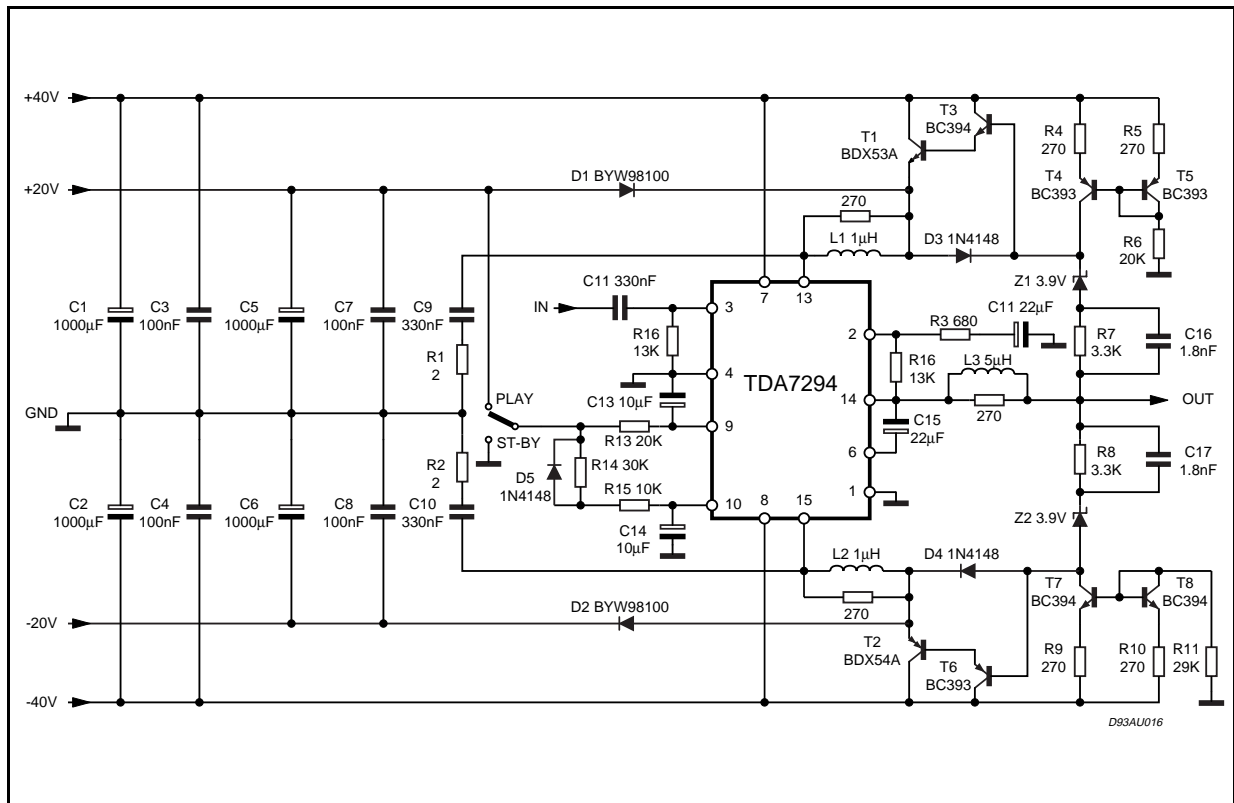
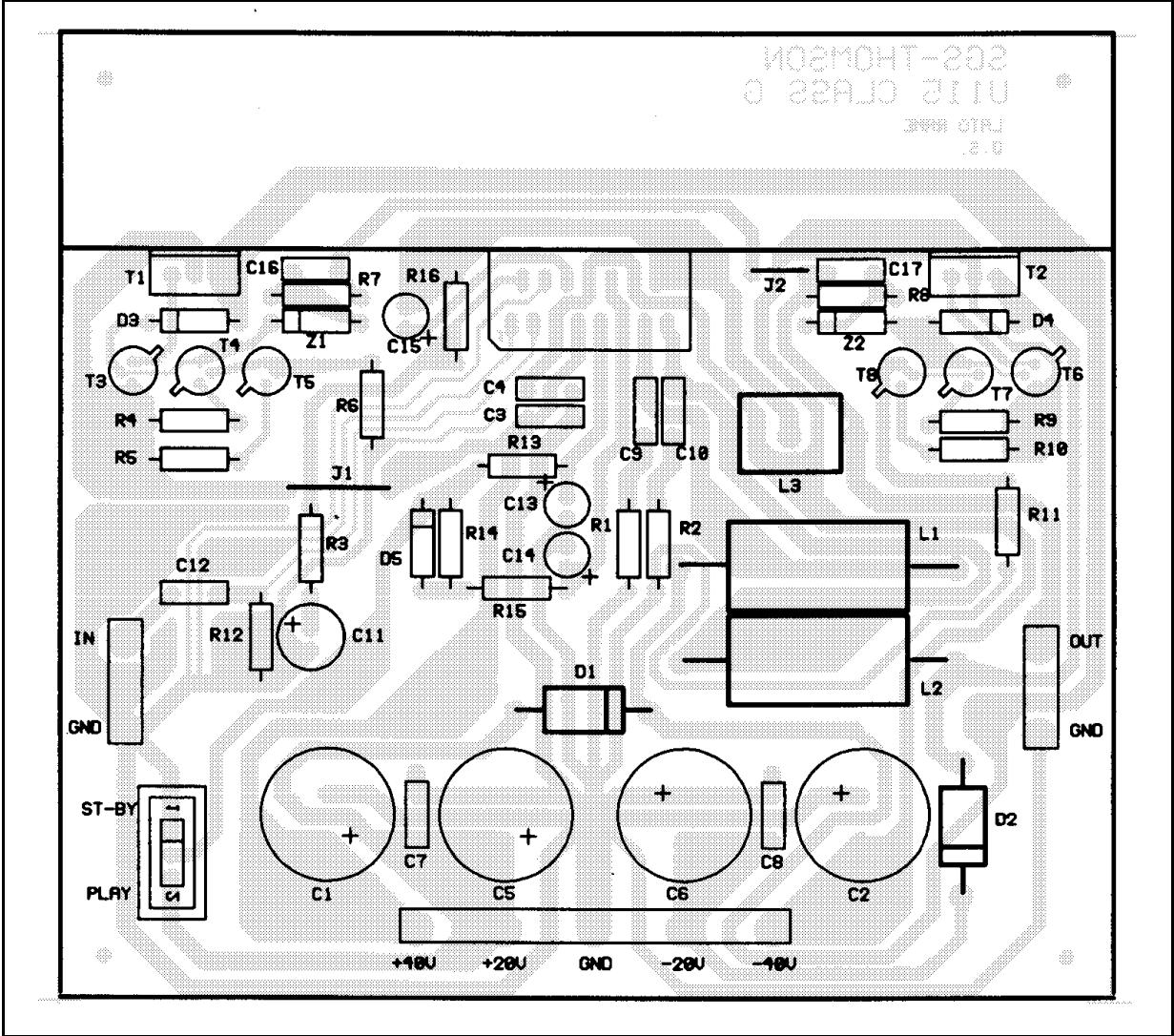


Figure 19: P.C.B. and Components Layout of the Circuit of figure 18 (1:1 scale)



diodes Z1,Z2 and resistors R7,R8 define the minimum drop across the power MOS transistors of the TDA7294. L1, L2, L3 and the snubbers C9, R1 and C10, R2 stabilize the loops formed by the "bootstrap" circuits and the output stage of the TDA7294.

In figures 21,22 the performances of the system in terms of distortion and output power at various frequencies (measured on PCB shown in fig. 19) are displayed.

The output power that the TDA7294 in high-efficiency application is able to supply at $V_s = +40V/+20V/-20V/-40V$; $f = 1 \text{ KHz}$ is:

- $P_{out} = 150 \text{ W} @ \text{T.H.D.} = 10 \%$ with $R_l = 4 \text{ Ohm}$
- $P_{out} = 120 \text{ W} @ \text{ " } = 1 \%$ " " "
- $P_{out} = 100 \text{ W} @ \text{ " } = 10 \%$ with $R_l = 8 \text{ Ohm}$
- $P_{out} = 80 \text{ W} @ \text{ " } = 1 \%$ " " "

Results from efficiency measurements (4 and 8 Ohm loads, $V_s = \pm 40V$) are shown by figures 23 and 24. We have 3 curves: total power dissipation, power dissipation of the TDA7294 and power dissipation of the darlington.

By considering again a maximum average output power (music signal) of 20W, in case of the high efficiency application, the thermal resistance value needed from the heatsink is 2.2°C/W ($V_s = \pm 40 \text{ V}$ and $R_l = 4 \text{ Ohm}$).

All components (TDA7294 and power transistors T1 and T2) can be placed on a 1.5°C/W heatsink, with the power darlington electrically insulated from the heatsink.

Since the total power dissipation is less than that of a usual class AB amplifier, additional cost savings can be obtained while optimizing the power supply, even with a high headroom.

Figure 20: Power Dissipation vs. Output Power

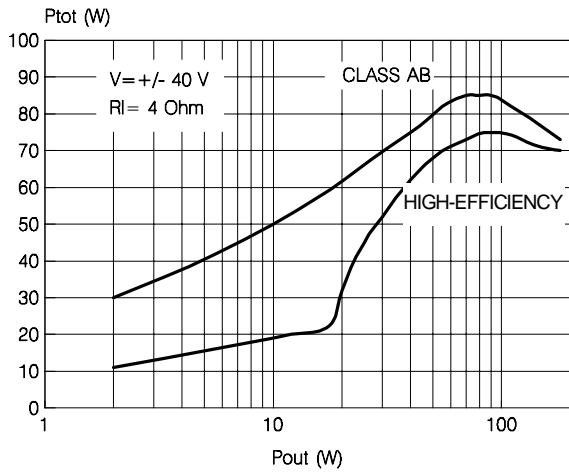


Figure 21: Distortion vs. Output Power

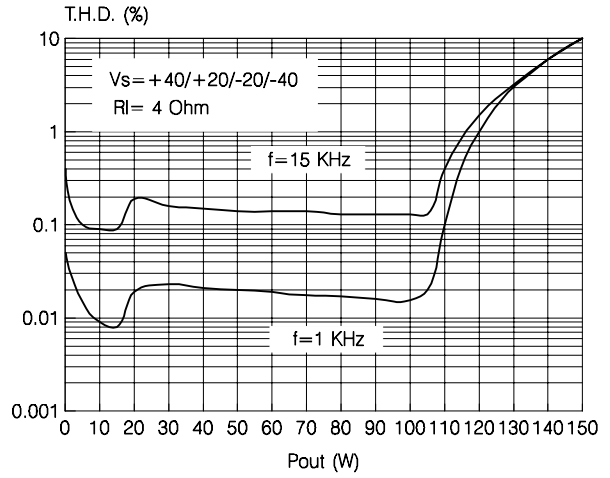


Figure 22: Distortion vs. Output Power

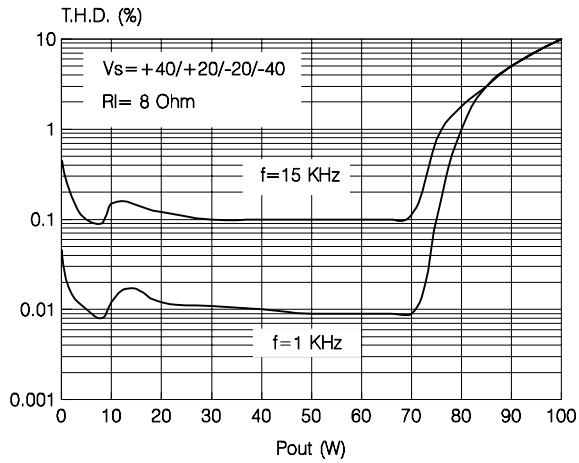


Figure 23: Power Dissipation vs. Output Power

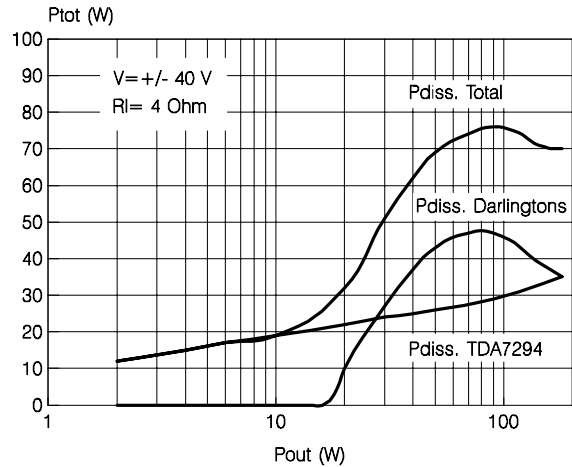
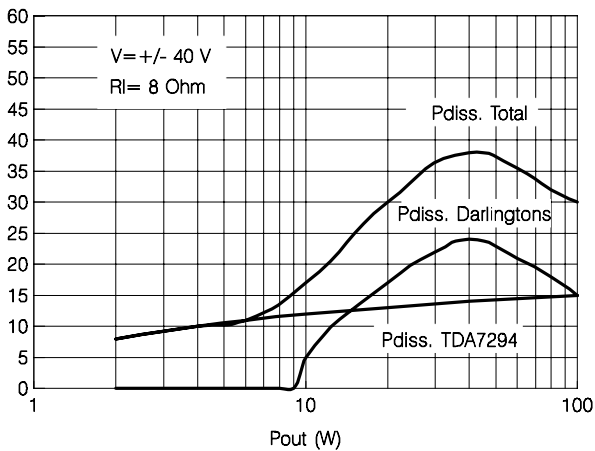


Figure 24: Power Dissipation vs. Output Power



BRIDGE APPLICATION

Another application suggestion is the BRIDGE configuration, where two TDA7294 are used, as shown by the schematic diagram of figure 25.

In this application, the value of the load must not be lower than 8 Ohm for dissipation and current capability reasons.

A suitable field of application includes HI-FI/TV subwoofers realizations.

The main advantages offered by this solution are:

- High power performances with limited supply voltage level.
- Considerably high output power even with high load values (i.e. 16 Ohm).

The characteristics shown by figures 27 and 28, measured with loads respectively 8 Ohm and 16 Ohm.

With $R_L = 8 \text{ Ohm}$, $V_s = \pm 25V$ the maximum output power obtainable is 150 W, while with $R_L = 16 \text{ Ohm}$, $V_s = \pm 35V$ the maximum P_{out} is 170 W.

Figure 25: Bridge Application Circuit

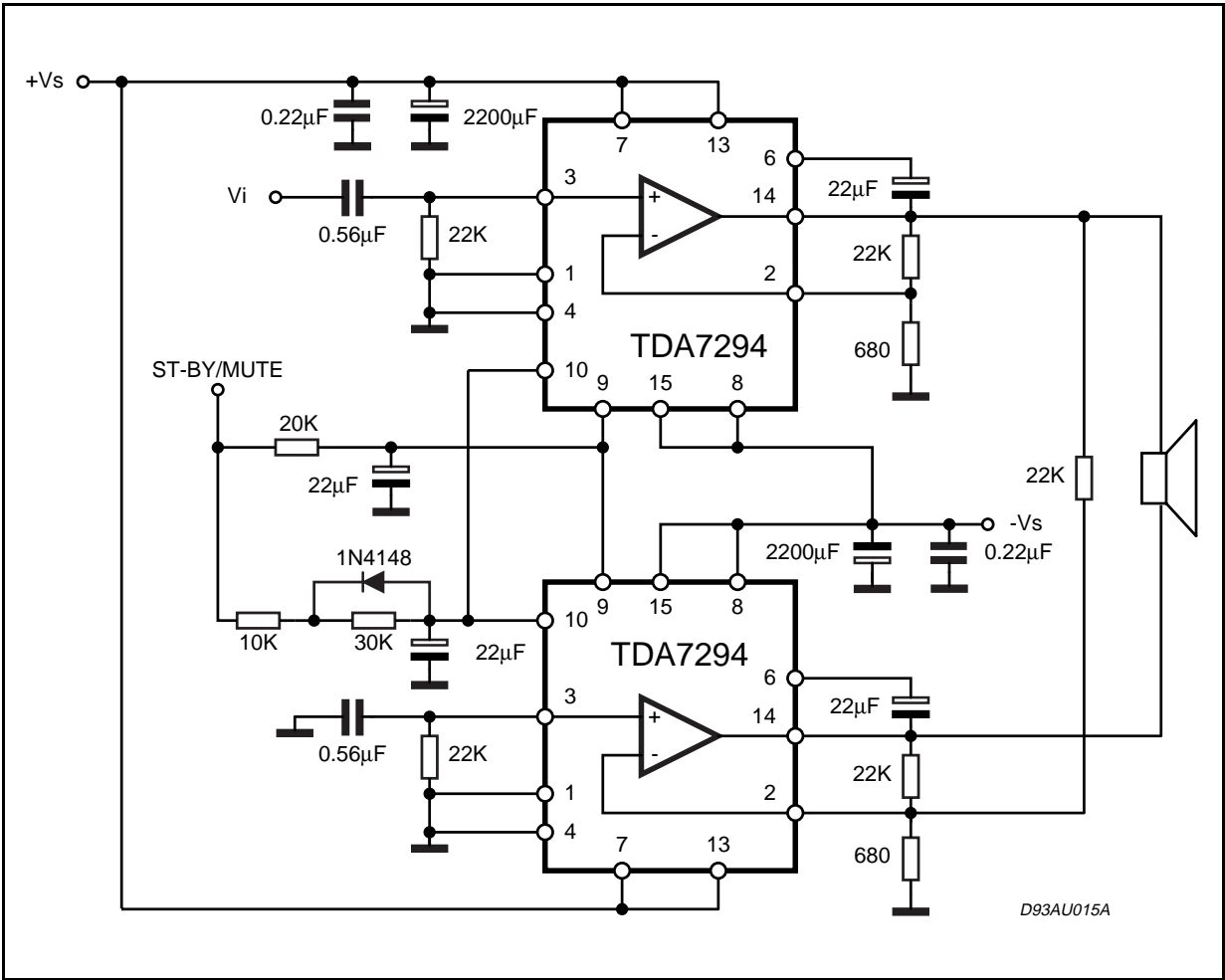


Figure 26: Frequency Response of the Bridge Application

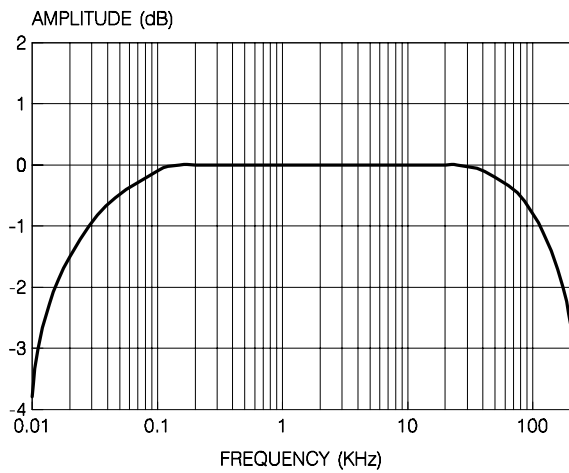


Figure 27: Distortion vs. Output Power

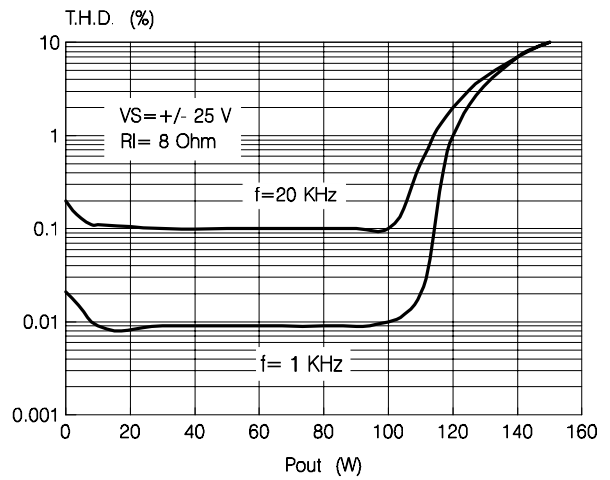
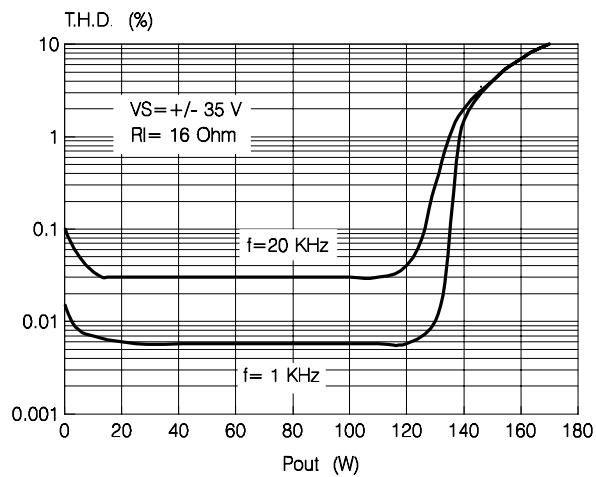
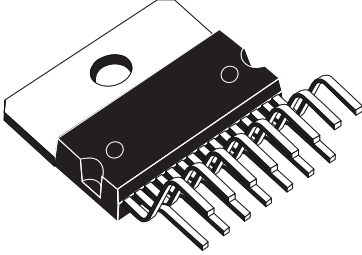


Figure 28: Distortion vs. Output Power

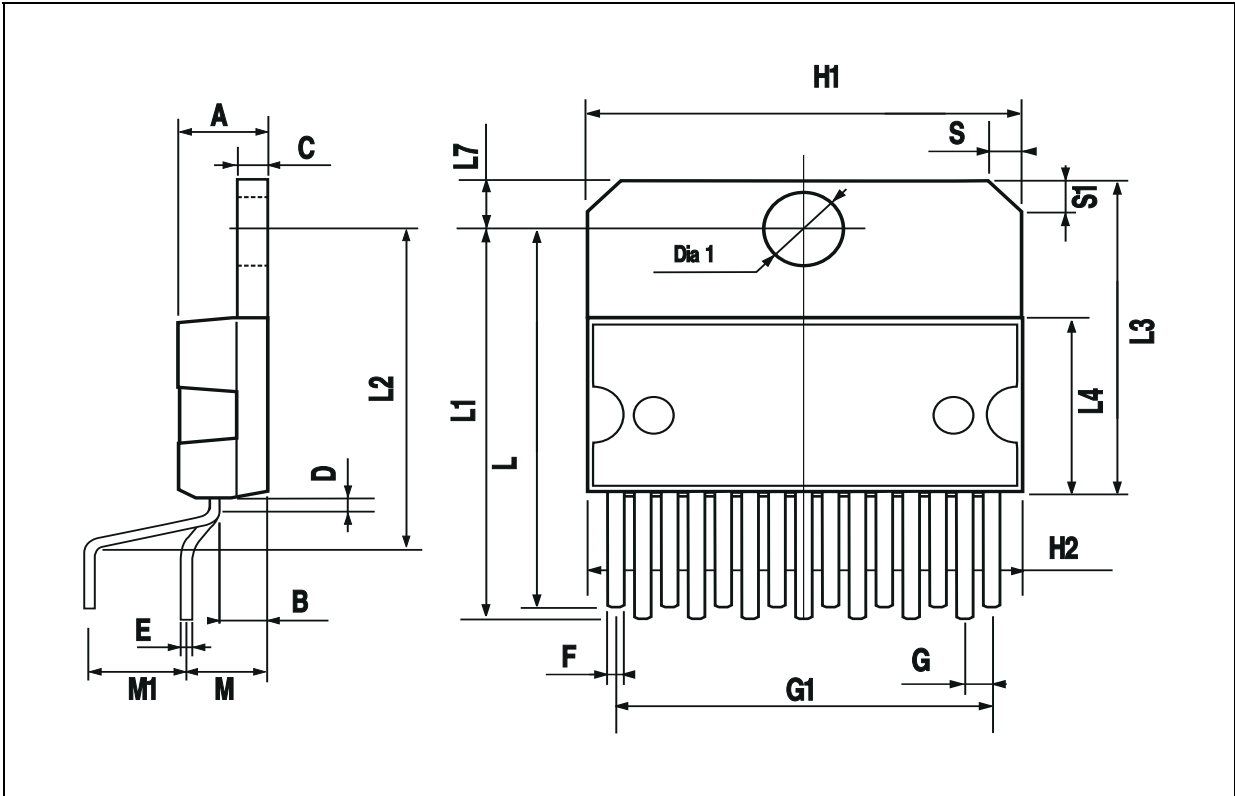


| DIM. | mm | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 5 | | | 0.197 |
| B | | | 2.65 | | | 0.104 |
| C | | | 1.6 | | | 0.063 |
| D | | 1 | | | 0.039 | |
| E | 0.49 | | 0.55 | 0.019 | | 0.022 |
| F | 0.66 | | 0.75 | 0.026 | | 0.030 |
| G | 1.02 | 1.27 | 1.52 | 0.040 | 0.050 | 0.060 |
| G1 | 17.53 | 17.78 | 18.03 | 0.690 | 0.700 | 0.710 |
| H1 | 19.6 | | | 0.772 | | |
| H2 | | | 20.2 | | | 0.795 |
| L | 21.9 | 22.2 | 22.5 | 0.862 | 0.874 | 0.886 |
| L1 | 21.7 | 22.1 | 22.5 | 0.854 | 0.870 | 0.886 |
| L2 | 17.65 | | 18.1 | 0.695 | | 0.713 |
| L3 | 17.25 | 17.5 | 17.75 | 0.679 | 0.689 | 0.699 |
| L4 | 10.3 | 10.7 | 10.9 | 0.406 | 0.421 | 0.429 |
| L7 | 2.65 | | 2.9 | 0.104 | | 0.114 |
| M | 4.25 | 4.55 | 4.85 | 0.167 | 0.179 | 0.191 |
| M1 | 4.63 | 5.08 | 5.53 | 0.182 | 0.200 | 0.218 |
| S | 1.9 | | 2.6 | 0.075 | | 0.102 |
| S1 | 1.9 | | 2.6 | 0.075 | | 0.102 |
| Dia1 | 3.65 | | 3.85 | 0.144 | | 0.152 |

OUTLINE AND MECHANICAL DATA

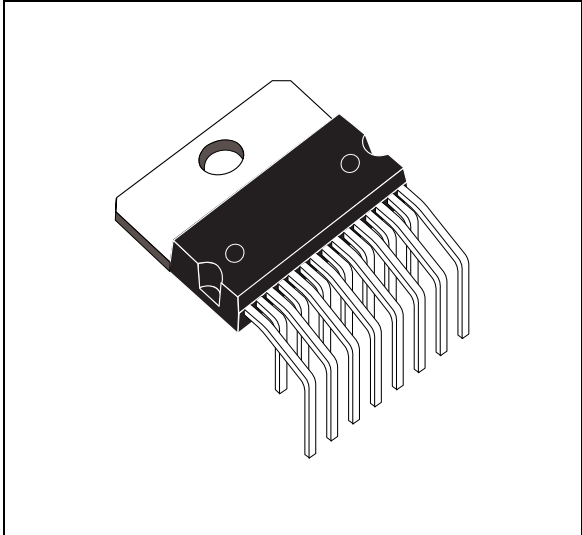


Multiwatt15 V

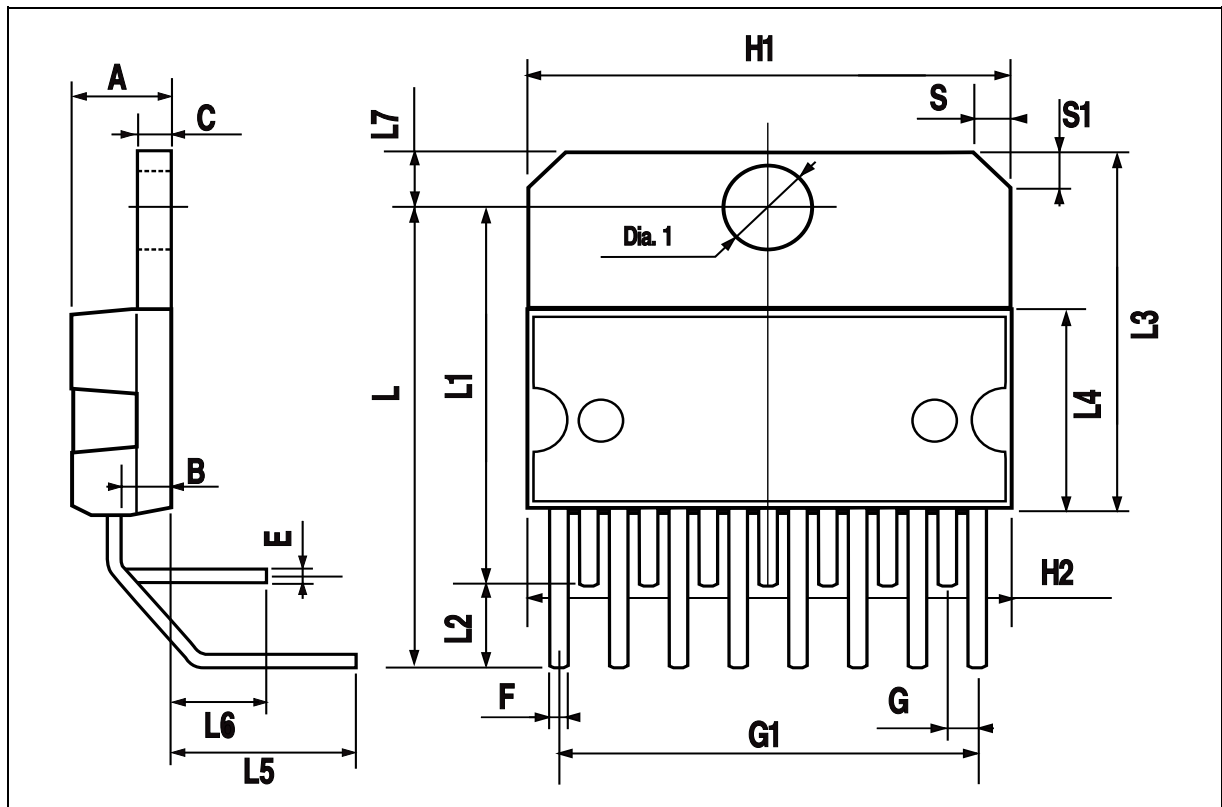


| DIM. | mm | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 5 | | | 0.197 |
| B | | | 2.65 | | | 0.104 |
| C | | | 1.6 | | | 0.063 |
| E | 0.49 | | 0.55 | 0.019 | | 0.022 |
| F | 0.66 | | 0.75 | 0.026 | | 0.030 |
| G | 1.14 | 1.27 | 1.4 | 0.045 | 0.050 | 0.055 |
| G1 | 17.57 | 17.78 | 17.91 | 0.692 | 0.700 | 0.705 |
| H1 | 19.6 | | | 0.772 | | |
| H2 | | | 20.2 | | | 0.795 |
| L | | 20.57 | | | 0.810 | |
| L1 | | 18.03 | | | 0.710 | |
| L2 | | 2.54 | | | 0.100 | |
| L3 | 17.25 | 17.5 | 17.75 | 0.679 | 0.689 | 0.699 |
| L4 | 10.3 | 10.7 | 10.9 | 0.406 | 0.421 | 0.429 |
| L5 | | 5.28 | | | 0.208 | |
| L6 | | 2.38 | | | 0.094 | |
| L7 | 2.65 | | 2.9 | 0.104 | | 0.114 |
| S | 1.9 | | 2.6 | 0.075 | | 0.102 |
| S1 | 1.9 | | 2.6 | 0.075 | | 0.102 |
| Dia1 | 3.65 | | 3.85 | 0.144 | | 0.152 |

OUTLINE AND MECHANICAL DATA



Multiwatt15 H



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